## Pure Phases of C<sub>3</sub>N<sub>4</sub> Synthesized at High Pressure and High Temperature

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Since A. Y. Liu and M. L. Cohen predicted that beta phase of C<sub>3</sub>N<sub>4</sub> may be comparable to diamond in hardness [1], and then D.M.Teter and R.J.Hemley predicted that cubic phase of  $C_3N_4$  will be harder than beta phase  $C_3N_4$  and a particular challenger to diamond [2], thousands of laboratories around the world launched into preparation of beta and cubic phase of C<sub>3</sub>N<sub>4</sub> by use of various experimental metholds [3]. Unfortunately, they failed to get pure phases of  $C_3N_4$  with stoichiometric ratio. We have obtained pure phases of graphite phase, beta phase of C<sub>3</sub>N<sub>4</sub> synthesized from carbon-natrogen organic compounds as stating material with different catalysts under high pressure and high temperature. We also got beta phase and cubic phase of C<sub>3</sub>N<sub>4</sub> starting from its graphite phase by use of laser heating method at high pressure and high temperature in DAC. Phase transitions from graphite phase  $C_3N_4$  to beta phase  $C_3N_4$ , and from beta to cubic  $C_3N_4$  under high pressure and room temperature have been investigated by XRD and electrical resistance measurement up to 104 GPa. A phase transition of C<sub>3</sub>N<sub>4</sub> looks like an electronic phase transition from direct band gap to indirect band gap by ab initio calculation of energy band at 40 GPa. The physical properties of C<sub>3</sub>N<sub>4</sub> will be reported in present paper.

## References:

- [1] A. Y. Liu, M. L. Cohen, Science, 1989, 245, 841-842
- [2] D. M. Teter, R. J. Hemley Science, 1996, 271, 53-55

[3] S. Matsumoto, E.-Q. Xie, F. Izumi Diamond and Related Materials 1999, 8,

1175–1182